

- ☞ L11: (15) 10 same 4
- ☞ L13: (46) 12 not 11
- ☞ L14: (15283) channel adj block \$4
- ☞ L15: (26905) channel adj (block \$4 stop \$4)
- ☞ L16: (28771) (split \$4 wrap \$4) adj gate
- ☞ L17: (4145) (split \$4 wrap \$4 multi) adj gate
- ☞ L18: (28888) (split \$4 wrap \$4 multi doubl \$4 side \$2) adj gate
- ☞ L19: (33) 15 with 18
- ☞ L20: (114) 15 same 18
- ☞ L21: (935) 15 and 18
- ☞ L22: (62) 20 same 8
- ☞ L23: (86816) ( (float \$4 adj (gate electrode plate wrap \$4) FG) charge \$4 adj (storage a
- ☞ L24: (24845) 2 same 23
- ☞ L25: (91169) (wordline "WL" ( (word digit control adj gate) adj line) (word near (read
- ☞ L28: (104972) ( (source data) adj line )
- ☞ L27: (882810) (bi bitline bit adj line readline read adj line sense adj line column)
- ☞ L28: (74091) control adj line
- ☞ L29: (45848) 25 same 27
- ☞ L30: (7160) 26 same 28
- ☞ L31: (341) 24 and 30
- ☞ L32: (5025376) second
- ☞ L33: (3848) 32 adj 0
- ☞ L34: (0) 31 and 33
- ☞ L35: (184) 31 and 9
- ☞ L36: (10826) 24 and 29
- ☞ L37: (220) 38 and 33

The screenshot shows the STN Explorer web application. At the top, there are buttons for "Index", "Query", "Browse", "Advanced", and "Clear". Below these, a search box contains the query "US:PCPUB; USPAT; EPO; JPO; DERWENT; ISM\_TDB". To the right of the search box are two checkboxes: "Phrases" and "Highlight all hit terms initially". Below the search box, it says "Default operator: OR". The main area displays "10 same 4" followed by a large handwritten-style number "117 2004". At the bottom, there is a navigation bar with links: "A CRS form", "A IS&R form", "Image", "Text", and "HTML".

	U	Inventor	Document Name	P	Title	Current	Current XR	Retrieval	S	C	P	Image	Doc.	P
1		Komori, Kazu	US 5427960	199503	Process for fabricating a semiconductor devi	438/257	257/E23.15		R	C	F	R	C	US 542796 F
2		Shukuri, Shoj	US 2004018	200409	Semiconductor integrated circuit device and	438/257			F	C	F	R	C	US 200401 F
3		Hanzawa, Sa	US 2004018	200402	Storage device	365/203			F	C	F	R	C	US 200401 F
4		Shukuri, Shoj	US 2003019	200319	Semiconductor integrated circuit device and	365/185			R	C	F	R	C	US 200301 F
5		Yi, Ji-Hye et	US 2003016	200302	Semiconductor memory device having a mult	257/316	257/E21.20		F	C	F	R	C	US 200301 F
6		Song, Seungh	US 2003013	200301	Scalable two transistor memory device	1/1	257/E21.68		R	C	F	R	C	US 200301 F
7		Yi, Ji-Hye et	US 2003003	200302	Semiconductor memory device having a mult	438/257	257/311		F	C	F	R	C	US 200300 F
8		Song, Seungh	US 2002019	200211	SCALABLE TWO TRANSISTOR MEMORY DE	365/83	257/E27.10		R	C	F	R	C	US 200201 F
9		Song, Seungh	US 6710465	200401	Scalable two transistor memory device	257/316	257/E21.68		F	C	F	R	C	US 671046 F
10		Yi, Ji-Hye et	US 6686240	200402	Semiconductor memory device having a mult	438/253	257/E21.20		F	C	F	R	C	US 668624 F